

## Descriptions

Double silicon NPN transistor in a SOT-363 Plastic Package.

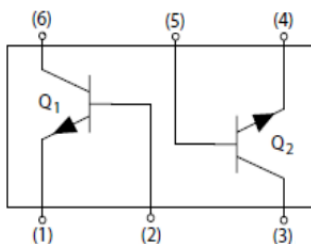
## Features

Low current, Low voltage.

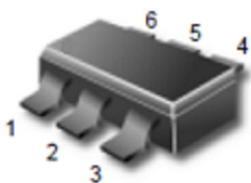
## Applications

General purpose amplifier and switching.

## Equivalent Circuit



## Pinning



PIN 1、 4 : Emitter

PIN 2、 5 : Base

PIN 3、 6 : Collector

## $h_{FE}$ Classifications & Marking

See Marking Instructions.

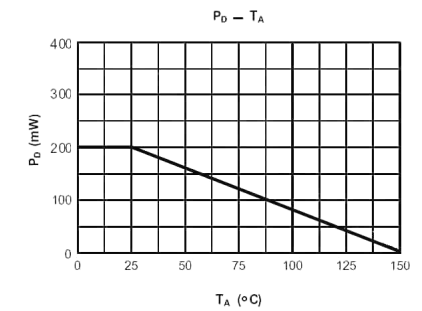
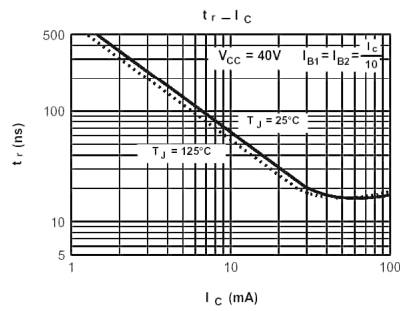
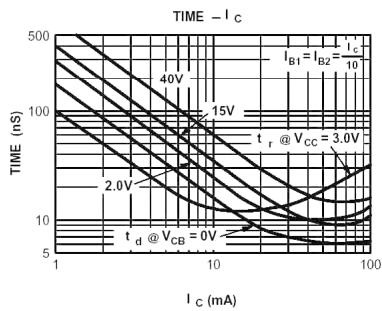
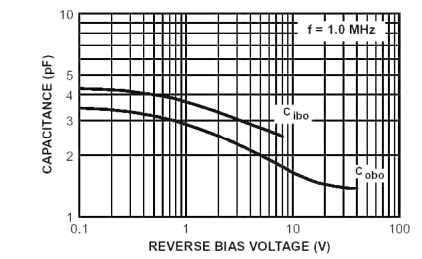
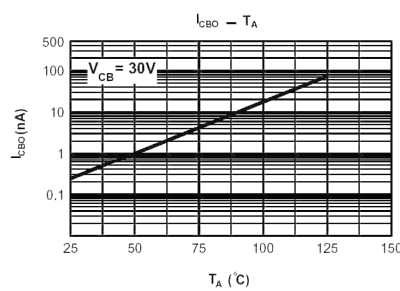
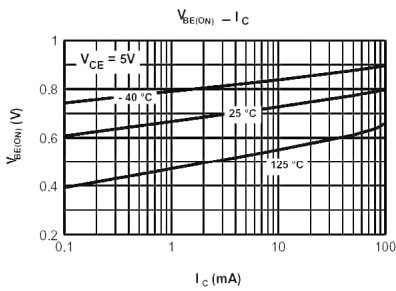
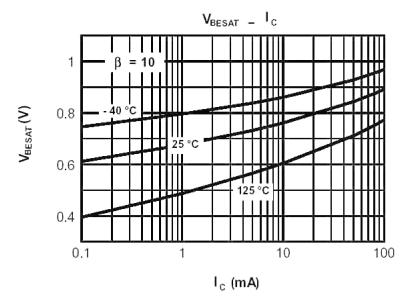
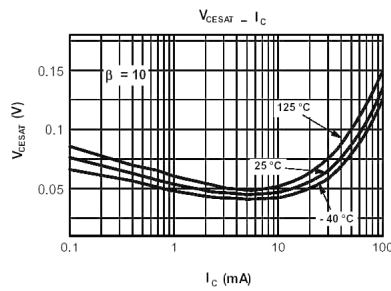
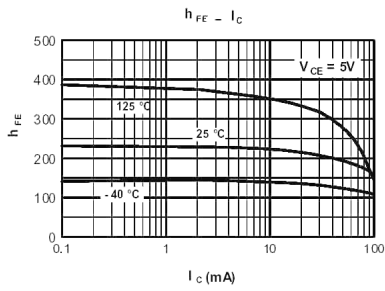
**Absolute Maximum Ratings(Ta=25°C)**

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	$V_{CBO}$	60	V
Collector to Emitter Voltage	$V_{CEO}$	40	V
Emitter to Base Voltage	$V_{EBO}$	6.0	
Collector Current	$I_C$	200	mA
Collector Power Dissipation	$P_C$	200	mW
	* $P_C$	350	mW
Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_{stg}$	-55~150	°C

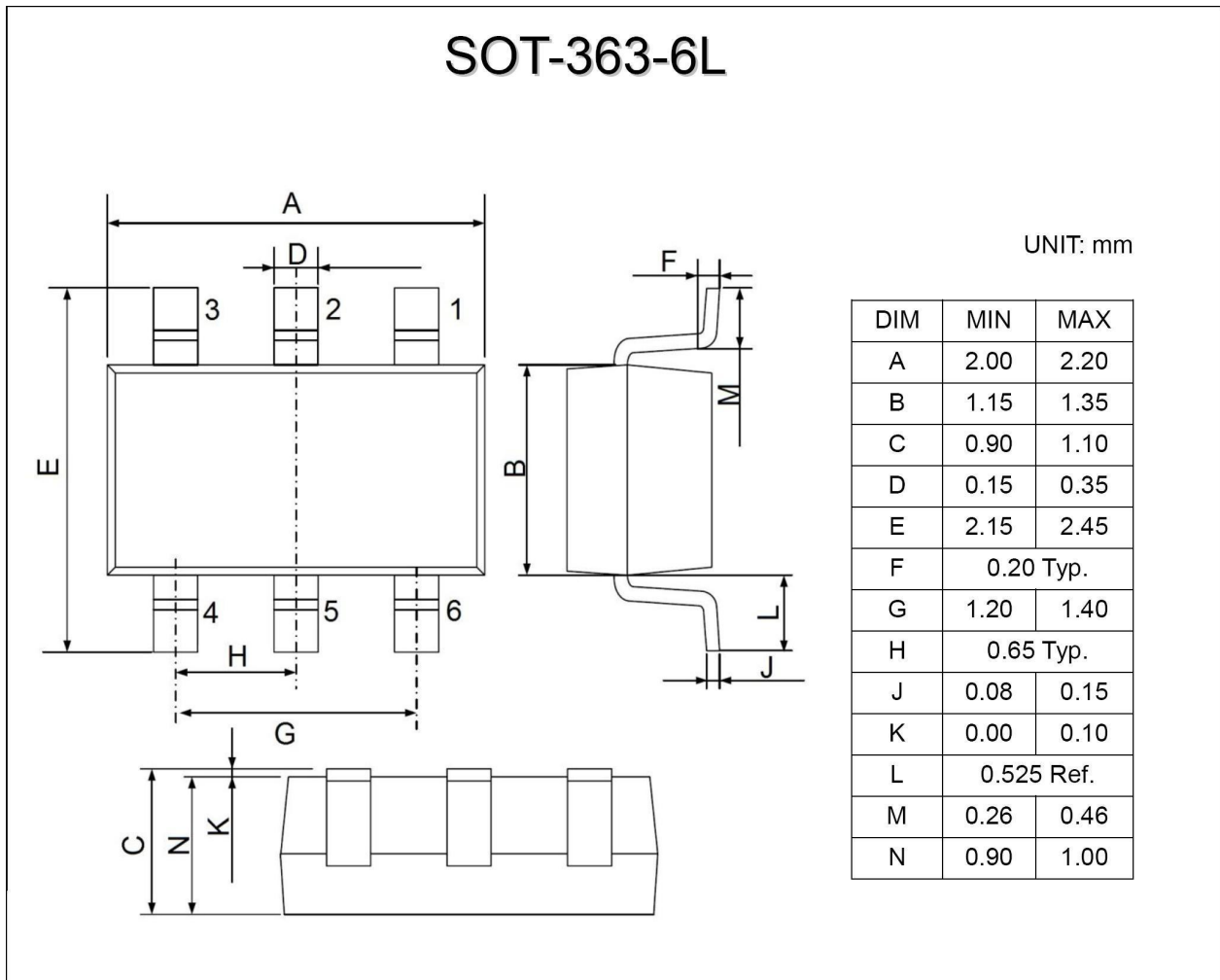
**Electrical Characteristics(Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	$V_{CBO}$	$I_C=10\mu A$ $I_E=0$	60			V
Collector to Emitter Breakdown Voltage	$V_{CEO}$	$I_C=1.0mA$ $I_B=0$	40			V
Emitter to Base Breakdown Voltage	$V_{EBO}$	$I_E=10\mu A$ $I_C=0$	6.0			V
Collector Cut-Off Current	$I_{CBO}$	$V_{CB}=30V$ $I_E=0$			0.05	$\mu A$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB}=3.0V$ $I_C=0$			0.05	$\mu A$
DC Current Gain	$h_{FE(1)}$	$V_{CE}=1.0V$ $I_C=10mA$	100		300	
	$h_{FE(2)}$	$V_{CE}=1.0V$ $I_C=100mA$	30			
	$h_{FE(3)}$	$V_{CE}=1.0V$ $I_C=50mA$	60			
	$h_{FE(4)}$	$V_{CE}=1.0V$ $I_C=1.0mA$	70			
	$h_{FE(5)}$	$V_{CE}=1.0V$ $I_C=0.1mA$	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=10mA$ $I_B=1.0mA$			0.2	V
	$V_{CE(sat)(2)}$	$I_C=50mA$ $I_B=5.0mA$			0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)(1)}$	$I_C=10mA$ $I_B=1.0mA$	0.65		0.85	V
	$V_{BE(sat)(2)}$	$I_C=50mA$ $I_B=5.0mA$			0.95	V
Transition Frequency	$f_T$	$V_{CE}=20V$ $I_C=10mA$ $f=100MHz$	300			MHz
Output Capacitance	$C_{ob}$	$V_{CB}=5.0V$ $f=1.0MHz$			4.0	pF
Storage Time	$t_{stg}$	$V_{CC}=3.0V$ $I_C=10mA$ $I_{B1}=-I_{B2}=1.0mA$			200	ns
Fall Time	$t_f$	$V_{CC}=3.0V$ $I_C=10mA$ $I_{B1}=-I_{B2}=1.0mA$			50	ns
Delay Time	$t_d$	$V_{CC}=3.0V$ $V_{BE}=0.5V$ $I_C=10mA$ $I_{B1}=1.0mA$			35	ns
Rise Time	$t_r$	$V_{CC}=3.0V$ $V_{BE}=0.5V$ $I_C=10mA$ $I_{B1}=1.0mA$			35	ns
Input Capacitance	$C_{ib}$	$V_{EB}=0.5V$ $f=1.0MHz$			8.0	pF

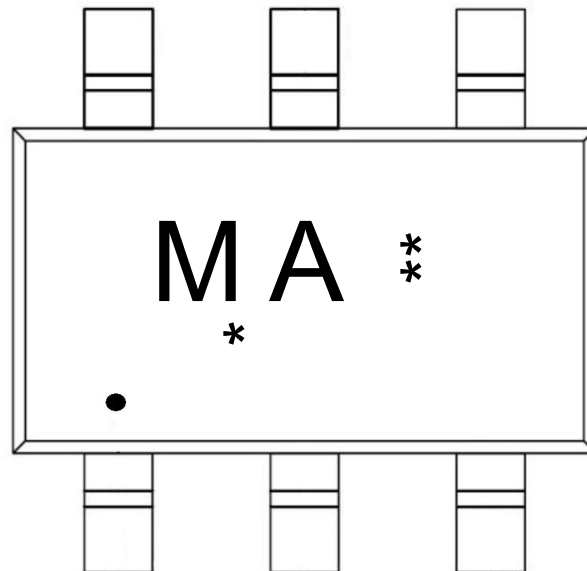
Electrical Characteristic Curve



Package Dimensions



Marking Instructions



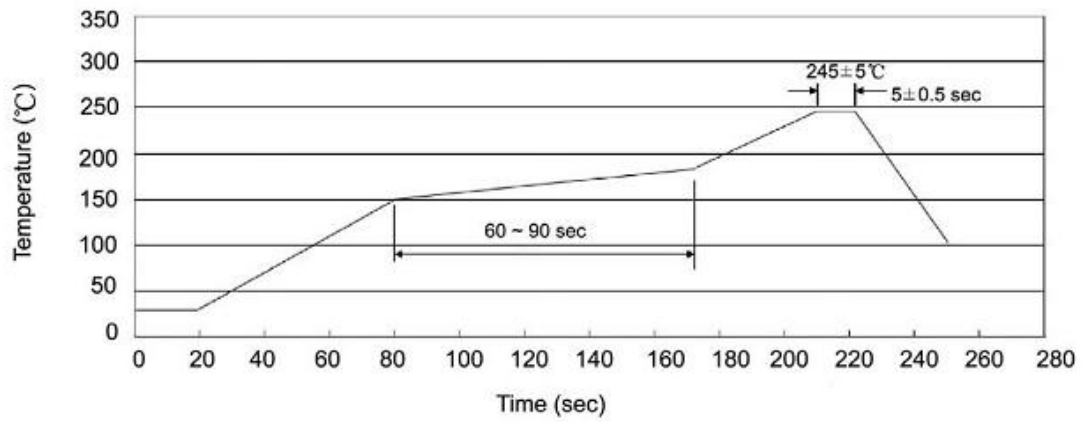
Note:

● : "1" Pin

MA : Product Type Code

\*\*\*: Lot No. Code, code change with Lot No.

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1. Preheating: 150~180°C, Time: 60~90sec.
2. Peak Temp.: 245±5°C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

Resistance to Soldering Heat Test Conditions

Temp.: 260±5°C

Time: 10±1 sec

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